

AMENDMENTS TO THE ABSTRACT

**Please replace the Abstract with the following paragraph:**

[Abstract]

~~The present invention relates to a growth method of nitride semiconductor layer~~  
~~comprising a first step for growing~~ Growing ~~a first nitride 5 semiconductor layer on an~~  
 ~~$\text{Al}_x\text{Ga}_y\text{In}_{1-x-y}\text{N}(0 < x < 1, 0 < y < 1, 0 < x+y < 1)$~~   $\text{Al}_x\text{Ga}_y\text{In}_{1-x-y}\text{N}(0 < x < 1, 0 < y < 1, 0 < x+y \leq 1)$  ~~layer, a~~  
~~second step for~~ reducing the thickness of the first nitride semiconductor layer by growth  
interruption and, ~~a third step for~~ growing a second nitride semiconductor layer having a band gap  
energy higher than that of the first nitride semiconductor layer on the first nitride semiconductor  
layer with the ~~[[to]]~~ reduced thickness and a light emitting device using the growth method.